

NPN Darlington Power Silicon Transistor

Rev. V4

Features

- Available in JAN, JANTX, JANTXV per MIL-PRF-19500/510
- TO-3 (TO-204AA) Package
- Suitable for High Voltage, High Current, High Speed Switching Applications



Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	I _C = 200 mA dc, L = 42 mH, f = 30 - 60 GHz 2N6249 2N6250 2N6251	V _{(BR)CEO}	V dc	_	200 275 350
Collector - Emitter Breakdown Voltage	$I_{C} = 200 \text{ mA dc, L} = 42 \text{ mH,}$ $f = 30 - 60 \text{ GHz}$ $R_{BE} = 50 \Omega$ $2N6249$ $2N6250$ $2N6251$	V _{(BR)CER}	V dc	_	225 300 375
Emitter - Base Cutoff Current	V _{EB} = 6 Vdc	I _{EBO}	μA dc	_	100
Collector - Emitter Cutoff Current	V _{CE} = 150 V dc, 2N6249 V _{CE} = 225 V dc, 2N6250 V _{CE} = 300 V dc, 2N6251	I _{CEO}	mA dc	_	1.0
Collector - Emitter Cutoff Current	V _{CE} = 225 V dc, V _{BE} = -1.5 V dc, 2N6249 V _{CE} = 300 V dc, V _{BE} = -1.5 V dc, 2N6250 V _{CE} = 375 V dc, V _{BE} = -1.5 V dc, 2N6251	I _{CEX1}	μA dc	_	10
Collector - Base Cutoff Current	V _{CE} = 300 V dc, 2N6249 V _{CE} = 375 V dc, 2N6250 V _{CE} = 450 V dc, 2N6251	І _{сво}	mA dc	_	0.5
Forward Current Transfer Ratio	I _C = 10 A dc, V _{CE} = 3 Vdc 2N6249 2N6250 2N6251	h _{FE1}	-	10 8 6	50 50 50
Collector - Emitter Sustaining Voltage	I_C = 10 A dc, I_B = 1.0 A dc, 2N6249 I_C = 10 A dc, I_B = 1.25 A dc, 2N6250 I_C = 10 A dc, I_B = 1.67 A dc, 2N6251	V _{CE(SAT)}	V dc	_	1.5
Base - Emitter Saturation Voltage	I_C = 10 A dc, I_B = 1.0 A dc, 2N6249 I_C = 10 A dc, I_B = 1.25 A dc, 2N6250 I_C = 10 A dc, I_B = 1.67 A dc, 2N6251	V _{BE(SAT)}	V dc	_	2.25



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Electrical Characteristics (T_A = +25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.		
Collector - Emitter Cutoff Current	$T_{A} = +125^{\circ}\text{C}$ $V_{CE} = 225 \text{ V dc, } V_{BE} = -1.5 \text{ V dc, } 2\text{N}6249$ $V_{CE} = 300 \text{ V dc, } V_{BE} = -1.5 \text{ V dc, } 2\text{N}6250$ $V_{CE} = 375 \text{ V dc, } V_{BE} = -1.5 \text{ V dc, } 2\text{N}6251$	I _{CEX2}	μA dc	_	90		
Forward - Current Transfer Ratio	$T_A = -55^{\circ}\text{C}$ $V_{CE} = 3 \text{ V dc}, I_C = 10 \text{ A dc}$ $2\text{N}6249$ $2\text{N}6250$ $2\text{N}6251$	h _{FE2}	-	5 4 3			
Dynamic Characteristics							
Small-Signal Short-Circuit Forward Current Transfer Ratio	I _C = 1 A dc, V _{CE} = 10 Vdc, f = 1 MHz	h _{FE}	-	2.5	15.0		
Open Capacitance Open Circuit	V _{CE} = 10 Vdc, I _C = 0, 100 kHz ≤ f ≤ 1 MHz	C _{obo}	pF	_	500		
Switching Characteristics							
Turn-On Time	V_{CC} = 200 Vdc; I_{C} = 10 A dc; I_{B} = 1.0 A dc, 2N6249 I_{B} = 1.25 A dc, 2N6250 I_{B} = 1.67 A dc, 2N6251	t _{on}	μs	_	2.0		
Turn-Off Time	V_{CC} = 200 Vdc; I_{C} = 10 A dc; I_{B} = 1.0 A dc, 2N6249 I_{B} = 1.25 A dc, 2N6250 I_{B} = 1.67 A dc, 2N6251	t _{off}	μs	_	4.5		
Safe Operating Area							
DC Tests: $T_C = +25 ^{\circ}\text{C}$, I Cycle,	t = 1.0 s (see figure 12 of MIL-PRF-19500)	/371)					
Test 1: $V_{CE} = 17.5 \text{ Vdc}, I_C = 10 \text{ A dc}$ Test 2: $V_{CE} = 30 \text{ Vdc}, I_C = 5.8 \text{ A dc}$ Test 3: $V_{CE} = 100 \text{ Vdc}, I_C = 0.3 \text{ A dc}$ Test 4: $V_{CE} = 200 \text{ Vdc}, I_C = 0.13 \text{ A dc}, \text{ (for 2N6249 only)}$ Test 5: $V_{CE} = 275 \text{ Vdc}, I_C = 0.09 \text{ A dc}, \text{ (for 2N6250 only)}$ Test 6: $V_{CE} = 350 \text{ Vdc}, I_C = 0.065 \text{ A dc}, \text{ (for 2N6251 only)}$							



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Absolute Maximum Ratings

Ratings	Symbol	2N6249	2N6250	2N6251	Units
Collector - Emitter Voltage	V _{CEO}	200	275	350	V dc
Collector - Base Voltage	V _{CBO}	300	375	450	V dc
Emitter - Base Voltage	V _{EBO}	6			V dc
Collector Current	Ic	10			A dc
Base Current	I _B	5			A dc
Total Power Dissipation @ $T_A = +25^{\circ}C$ @ $T_C = +25^{\circ}C^1$	P _T	6 175			W
Operating & Storage Temperature Range	T _J , T _{STG}	-65 to +200			°C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case ²	$R_{\theta JC}$	1.0°C/W

⁽¹⁾ For temperature-power derating curves, see figures 5 and 6 of MIL-PRF-19500/510

⁽²⁾ For thermal impedance curves, see figures 7, 8 and 9 of MIL-PRF-19500/510

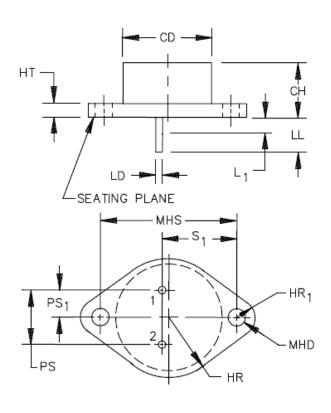


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Outline Drawing (TO-3)

Ltr	Dimensions			Note	
	Inc	ches Millin		neters	
	Min	Max	Min	Max	
CD		.875		22.23	
СН	.250	.450	6.35	11.43	
HR	.495	.525	12.57	13.34	
HR ₁	.131	.188	3.33	4.78	
НТ	.050	.135	1.27	3.43	
LD	.038	.053	0.97	1.35	3, 5
LL	.312	.500	7.92	12.70	3
L ₁		.050		1.27	5
MHD	.151	.161	3.84	4.09	
MHS	1.17	1.197	29.90	30.40	
PS	.420	.440	10.67	11.18	2
PS ₁	.205	.25	5.21	6.35	2, 3
S ₁	.665	.675	16.89	17.15	2



NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- These dimensions should be measured at points .050 (1.27 mm) to .055 (1.40 mm) below seating plane.
 When gage is not used, measurement will be made at seating plane.
- Two leads.
- Collector shall be electrically connected to the case.
- 5. LD applies between L₁ and LL maximum. Lead diameter shall not exceed twice LD within L₁.
- 6. In accordance with ASME Y14.5M, diameters are equivalent to φ symbology.
- 7. Terminal 1 is emitter; terminal 2 is base; case is collector.

FIGURE 1. Physical dimensions (similar to TO-3).



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